

Amendments to the Specification

Please replace the paragraph beginning on page 2, line 12 with the following amended paragraph:

Accordingly, in one aspect of the present invention, a method for fabricating a semiconductor device having a heat spreading layer with improved productivity is disclosed. The fabricating method for a semiconductor device of this invention includes forming a heat spreading material on a rear surface of the semiconductor wafer. The semiconductor wafer has a plurality of device areas and scribe lines which are arranged between the device areas. After the heat spreading material is formed on the rear surface of the semiconductor wafer, the semiconductor wafer is separated by the scribe lines.